Abstracts

A distributed, measurement based, nonlinear model of FETs for high frequencies applications

B. Mallet-Guy, Z. Ouarch, M. Prigent, R. Quere and J. Obregon. "A distributed, measurement based, nonlinear model of FETs for high frequencies applications." 1997 MTT-S International Microwave Symposium Digest 2. (1997 Vol. II [MWSYM]): 869-872.

For the first time, a FET nonlinear model, distributed along the gate length and extracted from pulsed I(V) and pulsed S-parameters measurements is presented. This model has led to a better prediction of power saturation mechanism and offers promising perspectives for intermodulation and nonlinear noise modeling at high microwave frequencies.

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